

## Transistors

## 10V Drive Nch MOS FET

## RDX060N60

## ●Structure

Silicon N-channel MOS FET

## ●Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Excellent resistance to damage from static electricity.

## ●Applications

Switching

## ●Packaging specifications

Type	Package	Bulk
	Code	—
	Basic ordering unit (pieces)	500
RDX060N60		○

## ●Absolute maximum ratings (Ta=25°C)

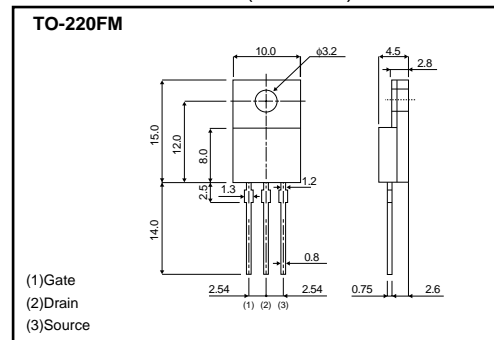
Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	600	V
Gate-source voltage		$V_{GSS}$	±30	V
Drain current	Continuous	$I_D$ *1	±6	A
	Pulsed	$I_{DP}$ *2	±24	A
Source current (Body diode)	Continuous	$I_S$	6	A
	Pulsed	$I_{SP}$ *2	24	A
Avalanche current		$I_{AS}$ *3	6	A
Avalanche energy		$E_{AS}$ *4	150	mJ
Total power dissipation (Tc=25°C)		$P_D$	40	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

\*1 Limited only by maximum temperature allowed \*2  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$   
 \*3  $L \leq 7.25mH$   $V_{DD}=90V$   $R_g=25\Omega$  \*4  $L \leq 7.25mH$   $V_{DD}=90V$   $R_g=25\Omega$  starting Tch=25°C

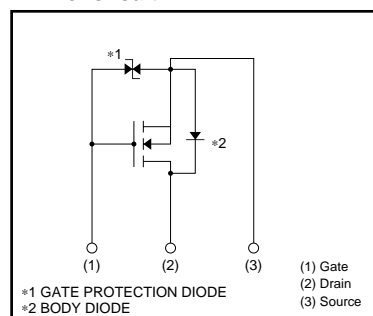
## ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.125	°C/W

## ●External dimensions (Unit : mm)



## ●Inner circuit



## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	–	–	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	25	μA	$V_{DS} = 600V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	2.0	–	4.0	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	–	0.9	1.2	Ω	$I_D = 3.0A, V_{GS} = 10V$
Forward transfer admittance	$ Y_{fs} ^*$	2.5	4.3	–	S	$V_{DS} = 10V, I_D = 3.0A$
Input capacitance	$C_{iss}$	–	950	–	pF	$V_{DS} = 25V$
Output capacitance	$C_{oss}$	–	110	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$	–	20	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	–	20	–	ns	$V_{DD} = 150V$
Rise time	$t_r^*$	–	14	–	ns	$I_D = 3.0A$
Turn-off delay time	$t_{d(off)}^*$	–	40	–	ns	$V_{GS} = 10V$
Fall time	$t_f^*$	–	28	–	ns	$R_L = 50\Omega$
Total gate charge	$Q_g^*$	–	25	–	nC	$V_{DD} = 300V$
Gate-source charge	$Q_{gs}^*$	–	6.5	–	nC	$V_{GS} = 10V$
Gate-drain charge	$Q_{gd}^*$	–	12	–	nC	$I_D = 6A$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}^*$	–	–	1.5	V	$I_S = 6A, V_{GS} = 0V$
Reverse recovery time	$t_{rr}^*$	–	500	–	ns	$I_{DR} = 6A, V_{GS} = 0V$
Reverse recovery charge	$Q_{rr}^*$	–	4.6	–	μC	$di/dt = 100A / \mu s$

\* Pulsed

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